$1.55\ \mu m$ Laser Diode with EA Modulator

HITACHI

ADE-208-834A (Z)

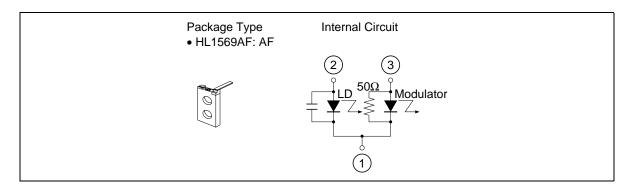
2nd Edition Dec. 2000

Description

The HL1569AF is a 1.55 μ m InGaAsP distributed-feedback laser diode (DFB-LD) with a multi-quantum well (MQW) structure. An electroabsorption (EA) modulator is integrated with the laser diode. It is suitable as a light source for high-bit-rate, long haul fiberoptic communication systems, such as 2.5 Gbps external modulation systems for up to 600 km.

Features

- Long wavelength output: $\lambda p = 1550 \text{ nm Typ}$
- High extinction ratio: 15 dB Min at $V_{R(EA)} = -2 V$
- Fast pulse response: $t_r/t_f \le 80 \text{ ps}$
- Dynamic single longitudinal mode: Sr = 40 dB Typ
- Package: open air package (chip on carrier) with micro strip-line





Absolute Maximum Ratings

 $(T_c = 25^{\circ}C)$

| Item | Symbol | Value | Unit |
|-----------------------------|--------------------|------------|------|
| LD forward current | I _F | 100 | mA |
| Laser diode reverse voltage | V _{R(LD)} | 2 | V |
| Modulator reverse voltage | V _{R(EA)} | 5 | V |
| Operating temperature | Topr | +10 to +40 | C° |
| Storage temperature * | Tstg | -40 to +85 | °C |

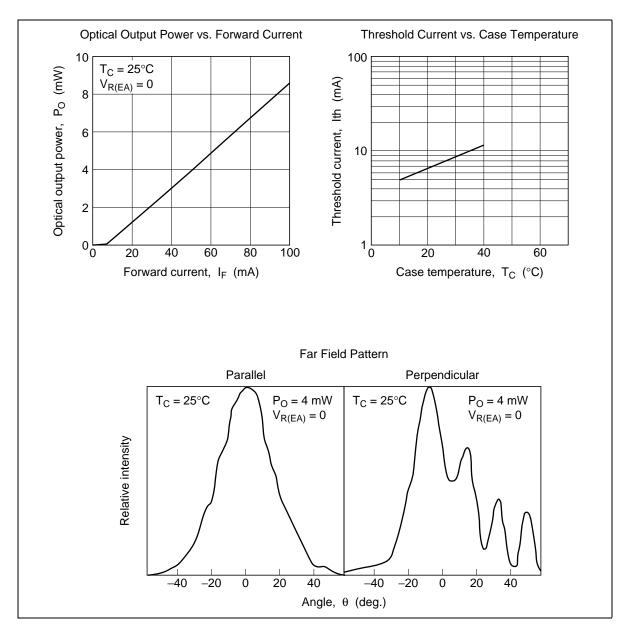
Note: without condensation

Optical and Electrical Characteristics

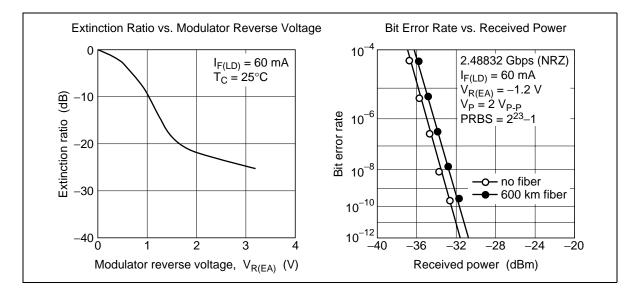
 $(T_c = 25^{\circ}C)$

| Item | Symbol | Min | Тур | Max | Unit | Test Conditions |
|---|------------------------|------|------|------|------|---|
| Threshold current | lth | — | 10 | 20 | mA | |
| Optical output power | Po | 4 | _ | _ | mW | $I_{_{F(LD)}} = 60 \text{ mA}, V_{_{R(EA)}} = 0 \text{ V}$ |
| Extinction ratio | ER | 15 | _ | _ | dB | $I_{_{F(LD)}} = 60 \text{ mA}, V_{_{R(EA)}} = 0/-2 \text{ V}$ |
| Lasing wavelength | λρ | 1530 | 1550 | 1570 | nm | 2.5 Gbps (NRZ) |
| Side-mode suppression ratio | Sr | 30 | 40 | _ | dB | 2.5 Gbps (NRZ) |
| Beam divergence parallel to the junction | θ// | — | 30 | _ | deg. | $P_{o} = 4 \text{ mW}, \text{FWHM}$ |
| Beam divergence parpendicular to the junction | θ⊥ | — | 40 | _ | deg. | $P_{o} = 4 \text{ mW}, \text{FWHM}$ |
| Rise time | t, | _ | — | 80 | ps | 2.5 Gbps (NRZ) |
| Fall time | t _f | — | — | 80 | ps | 2.5 Gbps (NRZ) |
| Cutoff frequency | S ₂₁ | 4 | | _ | GHz | $I_{_{F(LD)}} = 60 \text{ mA}, V_{_{R(EA)}} = -1 \text{ V}$ |
| RF return loss | S ₁₁ | 10 | _ | _ | dB | $\begin{split} I_{_{F(LD)}} &= 60 \text{ mA}, V_{_{R(EA)}} = -1 V, \\ f &\leq 3 GHz \end{split}$ |

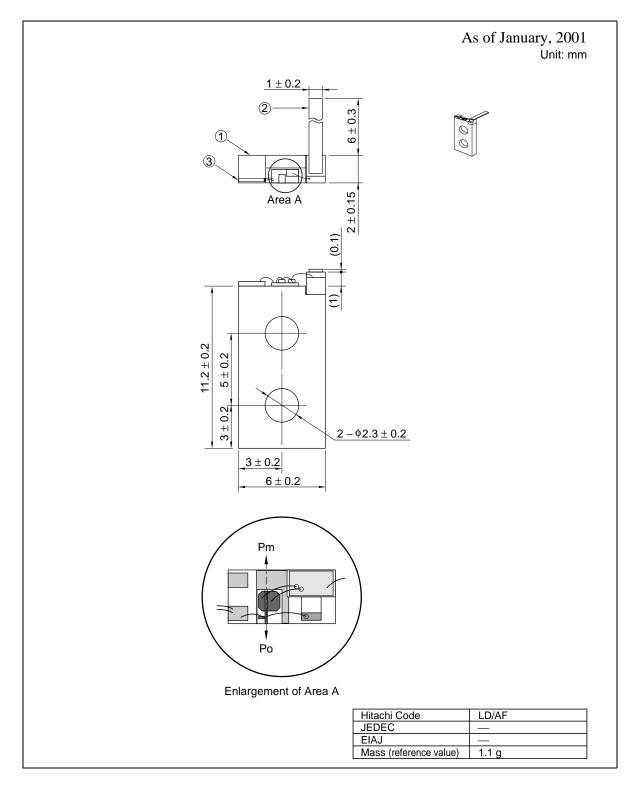
Typical Characteristic Curves



Typical Characteristic Curves (cont)



Package Dimensions



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- 1. The laser light is harmful to human body especially to eye no matter what directly or indirectly. The laser beam shall be observed or adjusted through infrared camera or equivalent.

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